

PERFORMANCE SPECIFICATION

SEMICONDUCTOR DEVICE, DIODE, SILICON, POWER RECTIFIER, FAST RECOVERY
TYPES 1N5812, 1N5814, 1N5816, AND R VERSIONS
JAN, JANTX, JANTXV, JANHC, JANKC, AND JANS

This amendment forms a part of MIL-PRF-19500/478D, dated 26 May 1997 and is approved for use by all Departments and Agencies of the Department of Defense.

PAGE 3

- * Figure 1, dimension table, delete letter CD in its entirety and substitute

" | CD | 0.265 | 0.424 | 6.74 | 10.77 | | "

- * Figure 1, dimension table, delete letter CD* in its entirety and substitute:

" | CD₁ | 0.265 | 0.437 | 6.74 | 11.10 | | "

- * Figure 1, dimension table, add letter b at end of table.

" | b | | 0.250 | | 6.35 mm | 4 | "

PAGE 11

- * 4.4.3, delete subgroup C3 in it's entirety.

PAGE 12

Table 1, subgroup 3, conditions column for $V_{(BR)2}$; delete " $I_R = 100 :A dc$ " and substitute " $I_R = 100 \mu A dc$ ".

The attached insertable replacement pages listed below are replacements for stipulated pages. When the new pages have been entered in the document, insert the amendment as the cover sheet to the specification.

<u>Replacement page</u>	<u>Page replaced</u>
1	1
2	2

MIL-PRF-19500/478G
AMENDMENT 2

NOTE: The margins of this amendment are marked with asterisks to indicate where changes from the previous amendment were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous amendment.

Custodians:

Army - CR
Navy - EC
Air Force - 17

Preparing activity:
DLA - CC

(Project 5961-2014)

Review activities:

Army - AR, MI, SM
Navy - AS, CG, MC
Air Force - 19, 85, 99
NASA - NA

MIL-PRF-19500/478G
AMENDMENT 2

The documentation process conversion measures necessary to comply with this revision shall be completed by 26 August 1997

INCH-POUND

MIL-PRF-19500/478G
26 May 1997
SUPERSEDING
MIL-S-19500/478F
3 March 1995

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1. SCOPE

1.1 Scope. This specification covers the performance requirements for silicon, fast recovery power rectifier diodes. Four levels of product assurance are provided for each device type as specified in MIL-S-19500. Two product assurance levels are provided for die.

1.2 Physical dimensions. See 3.3 (D0-4 and unencapsulated die).

1.3 Maximum ratings.

Types	V _R	V _{RWM}	I _O 1/	I _{FSM}	t _{rr}
			T _C = +100°C	T _C = +100°C t _p = 8.3 ms	
	V _{dc}	V (pk)	A _{dc}	A _{dc}	ns
1N5812, R	50	50	20	400	35
1N5814, R	100	100	20	400	35
1N5816, R	150	150	20	400	35

1/ Derate linearly, 250 mA/°C from +100°C to +150°C, and 300 mA/°C above +150°C.
Storage temperature: T_{STG} = -65°C to +175°C.
Operating temperature: T_J = -65°C to +175°C.
Barometric pressure reduced (altitude operation): 8 mmHg.
R_{θJC} = 1.5°C/W maximum.

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAT, 3990 East Broad Street, Columbus, OH 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

AMSC N/A

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FSC 5961

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MIL-PRF-19500/478G
AMENDMENT 2

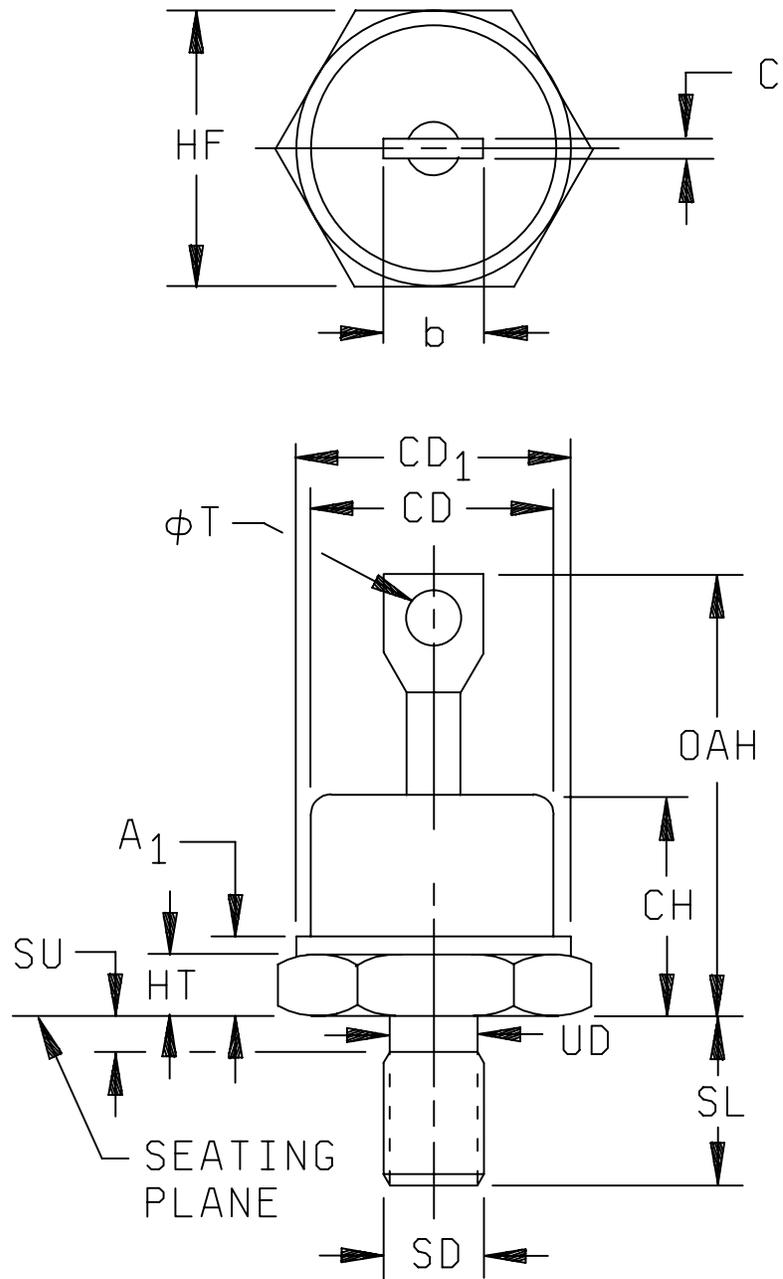


FIGURE 1. Physical dimensions (DO-4).

Supersedes page 2 of MIL-PRF-19500/478G
dated 26 May 1997